## On the hot-electron regime in one-dimensional nano-transistors

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## Abstract

The high-frequency transconductance and current noise of top-gated single carbon nanotube transistors have been measured and used to investigate hot electron effects in one-dimensional transistors. Results are in good agreement with a theory of ballistic nano-transistor. In particular the prediction of a large transconductance correction to the Johnson-Nyquist thermal noise formula is confirmed experimentally. Experiment shows that nanotube transistors can be used as fast charge detectors for quantum coherent electronics with a resolution of  $13\mu e/\sqrt{\text{Hz}}$  in the 0.2–0.8 GHz band.

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Our understanding of electron transport in nano-structures has strongly benefited from single shot detection like in the recent electron counting in quantum dot devices [1]. In these experiments charges are trapped in the dot over microseconds which allows for real time fieldeffect detection by a nearby transistor. This time scale corresponds to sequential transport, improvements in sensitivity and bandwidth are needed to probe the coherent regime for a future quantum electronics where ballistic electrons are delocalized in the conductors [2]. Fast, charge sensitive nano-transistors made of quantum wires are fast charge sensors and good candidates for such an on-the-fly detection, provided one can understand and control the noise mechanisms that limits their resolution.

A well-known realization of the few-channel transistor paradigm is the single carbon nanotube transistor [3], especially top gated transistors which work at high frequency [4] (see review in [5]). Ultimate gate coupling and finite density of states push nanotransistors close to the quantum limit where gate capacitance  $C_g = \beta C_q$  approaches the quantum capacitance  $C_q$  ( $\beta \leq 1$ )[4]. An important limiting factor of sensitivity is thermal noise from hot electrons which is prominent due to poor energy relaxation in low-dimensional conductors [6, 7]. Effect of dissipation can been investigated by noise thermometry [8] but also by measuring the local phonon population generated at finite bias  $V_d$  [9]. The nanotransistor geometry offers an opportunity to revisit hot electron effects using the additional control of electronic transmission.

The noise thermometry approach of electronic population relies on assumption of a thermal distribution and the Johnson-Nyquist formula  $S_I = 4g_n k_B T_e$  which relates the current noise spectral density  $S_I$  to the electronic temperature  $T_e$  via a so-called "noise conductance"  $g_n$ . At equilibrium or in metals one has  $g_n = g_d$ , the differential drain conductance. The situation is different in gated semiconductors where an additional contribution arises, at finite bias, associated with transconductance  $g_m = \partial I_d / \partial V_g$  where  $I_d$  is the drain current and  $V_g$  the gate voltage. This term depends a priori on geometry, at least for the 3D and 2D transistors [10, 11]. We show here that situation is different at 1D and that a simple relation between  $g_d$ ,  $g_m$  and  $g_n$  exists for nanotransistors which only brings in the gate coupling factor  $\beta$ .

The paper reports on current noise and transconductance of top-gated single nanotube transistors studied at the valence band edge (gate voltage  $V_g \gtrsim 0$  in Fig.2). Measurements were carried in a broad GHz bandwidth to get rid of  $1/f^{\alpha}$  low frequency noise and contact resistances. The hot electron effects show up both in the thermal noise and the width of the transconductance peak at the onset of hole conduction. Using a ballistic 1-dim nanotransistor model we shall obtain a generalized Johnson-Nyquist noise formula in the form,

$$S_I = 4 \left( g_d + g_m / 2\beta \right) k_B T_e$$
 (1)

Eq.(1) is confirmed experimentally by independent measurements of noise, transconductance and temperature at high bias. Noise can be alternatively compared to dc current and characterized by a pseudo Fano factor  $\tilde{F} = S_I/2eI_d$ ;  $\tilde{F} = 1$  being the Poisson limit of independent electrons. The hot electron regime shows up in our 1D transistor by  $\tilde{F} \gtrsim 1$  at low bias and significant Fermi suppression ( $\tilde{F} \simeq 0.7$ ) at high bias.

A symmetric double gate design is used (Fig.1 and Refs.[4]) on high mobility CVDgrown nanotubes (diameter  $d \sim 2$ . nm) with a top gate (length  $L_g = 0.3 \mu$ m) on thin  $AlO_x$  oxide (thickness  $t_{ox} \simeq 6$  nm). The cryogenic setup includes a low noise amplifier (LNA) fitted to a 200–50 Ohms matching transformer for an improved current resolution. Resistive loads are used for flat-band response in the 0.1–0.8 GHz bandwidth. The 200 Ohms output shunt ensures voltage bias and provides an auxiliary white noise source for insitu calibration. DC conductance  $g_d(0)$  and transconductance  $g_m(0)$  are obtained from the current  $I_d(V_g, V_d)$  characteristics (Fig.2-inset). RF transconductance  $g_m^{RF}$  (Fig.2) is deduced from transmission  $2Z_0 g_m^{RF}$ . Besides, this setup has no access to reflectometric measurement of the RF conductance  $g_d^{RF}$ . The gate capacitance,  $C_g/L_g \simeq 0.07 \pm 0.02$  fF/ $\mu$ m, was measured at room temperature on similar samples from the same batch [4]. With  $C_q/L_g =$  $8e^2/hv_F = 0.4 \text{ fF}/\mu \text{m} (v_F \simeq 8 \times 10^5 \text{ m/s})$  we deduce the value of the gate coupling coefficient  $\beta \simeq 0.2$ . We have used negative drain bias, which shows lower  $1/f^{\alpha}$  noise and symmetric gate bias conditions with an applied voltage  $\tilde{V}_g = V_g + V_d/2$ . DC current and current noise are taken by reference to the pinch-off value ( $V_g = +1$  V). As seen in Fig.2 the sample shows large  $g_m \simeq 30 \ \mu\text{S}$  at  $V_d = -0.9 \text{ V}$ , typically 3-times larger than the dc ones. They are only 50% larger than the room temperature values [4], which is an indication of a hot electron regime at 4K. Quantitative analysis of the  $g_m(V_g)$  data using theoretical expression (2) below (solid lines in Fig.2), confirms quasi-ballistic transport with  $T_e \simeq 300$  K.

We first discuss the bias dependence of current and noise for the transistor in the open state ( $V_g = -0.5$  V in Fig.3) and at transconductance maximum ( $V_g = +0.5$  V in Fig.4). The open state mimics a metallic wire with a finite transmission,  $D \sim 0.1$  at low bias, due to contact barriers. As seen in Fig.3, a poissonian limit is observed up to  $|V_d| \gtrsim 0.4$  V followed by a noise plateau. The saturation regime for noise and current will be discussed elsewhere. At this large energy scale one can readily exclude quantum tunneling and analyze data in terms of classical shot noise. An overestimate of electronic temperature  $k_B T_e/eV_d \lesssim 0.6$  can be deduced from Eq.(1) taking  $g_d^{RF} \gtrsim g_d(0)$  and  $g_m = 0$ . Indeed, this ratio is larger than a rough estimate,  $k_B T_e/eV_d \sim \sqrt{6D/\pi^2} \sim 0.25$ , from Wiedemann-Franz thermal resistance [12]. Numbers show that a hot electron regime is already at work in the open state. A similar  $S_I(V_d)$  dependence is observed at the transconductance maximum in Fig.4. An important difference comes from the existence of a first plateau for  $|V_d| = 0.1-0.3$  V, corresponding to a shot-noise suppression factor  $\tilde{F} \simeq 0.7$ . The two step increase of noise at the band edge is reminiscent of the subband structure carbon nanotubes, with an intersubband of 0.3–0.5 eV for our small gap nanotube. To keep true 1D conditions we shall restrict ourself below to the first subband with  $|V_d| \lesssim 0.3$  V.

For quantitative analysis of the RF current, noise and transconductance data in Fig.4 we rely on a simple ballistic 1D nano-transistor model. The nanotube is described as a fourfold degenerate 1D channel decomposed in three sections: a central part covered by the top-gate which acts as a classical barrier and two ungated leads constituting the drain and source reservoirs. Leads are populated with Fermi distributions  $f_s(E)$  and  $f_d(E) = f_s(E + eV_d)$  and the barrier (height  $\Phi$ ) acts as an high-pass energy filter with ballistic high energy electrons  $(E > \Phi)$  and reflected low energy ones  $(E < \Phi)$ . With these assumptions and scattering theory [13] one can easily calculate current and noise to deduce differential conductance  $g_d = \frac{4e^2}{h}f_d(\Phi)$ , transconductance

$$g_m = \beta \frac{4e^2}{h} [f_s(\Phi) - f_d(\Phi)] \qquad , \tag{2}$$

and noise conductance  $g_n = \frac{2e^2}{h} [f_s(\Phi) + f_d(\Phi)]$ . As explained in Fig.1, the gate coupling coefficient  $\beta = (1/e)\partial\Phi/\partial V_g = C_g/C_q$ . The three conductances depend only on the drain and source occupation numbers (at  $E = \Phi$ ) and obey the constitutive relation  $g_n = g_d + g_m/2\beta$ giving rise to Eq.(1). Details of screening, which are encoded in the  $\Phi(V_d, V_g)$  functional, or temperature  $T_e(V_d, V_g)$  in  $f(\Phi)$ , disappear in Eq.(1) which can be regarded as universal for 1D transistors. Noise can also be compared to dc current and expressed in terms of pseudo Fano factor  $\mathcal{F} = S_I/2eI_d$ . At low bias one has  $g_m < 2\beta g_d$  and  $\mathcal{F} = \coth(eV_d/2k_BT_e) \lesssim 1.3$ (for  $2k_BT_e/eV_d \lesssim 1$ ). At high bias,  $g_m \gg 2\beta g_d$  whenever  $f_d(\Phi) \ll f_s(\Phi) \lesssim 1$  which gives rise to Fermi suppression of noise due to the  $(1 - f_s)$  reduction factor [13].

Fig.4 compares the main experimental results of the paper, namely  $I_d$ ,  $S_I$  and  $g_m$ , at the onset of transistor conduction. The model accounts well for the observed poissonian regime at low bias and shot noise suppression at intermediate bias. Taking the electronic temperature from transconductance data in Fig.2 we can compare noise and transconductance to test Eq.(1). We work in the middle of the plateau ( $V_d = -0.2 \text{ V}$ ) where  $S_I/2e \simeq 1.46 \pm 0.1 \ \mu\text{A}$ ,  $g_m = 8.6 \ \mu\text{S}$ ,  $V_{Te} = k_B T_e/e\beta \simeq 0.14 \text{ V}$  and  $g_m V_{Te} \simeq 1.2 \pm 0.2 \ \mu\text{A}$ , in good agreement with prediction  $S_I/2e \gtrsim g_m V_{Te}$  of Eq.(1). By comparison standard noise thermometry would give a smaller value  $S_I/2e = 2g_d k_B T_e/e \simeq 0.5 \ \mu\text{A}$  ( $g_d \simeq 9 \ \mu\text{S}$ ). We take this agreement as a strong support for the 1D model. Further experimental investigation should involve direct measurement of  $g_d(\omega)$  to test formula (1) over the full bias range including the crossover  $g_m \lesssim 2\beta g_d$ .

The hot electron noise is important for understanding dissipation at 1D but also for applications of single nanotube transistors, in particular to estimate its charge resolution,  $\delta q_{rms} = \sqrt{S_I}C_g/g_m$ . The best signal to noise conditions for our device correspond to a 0.3 V bias with a dissipation  $I_dV_d \sim 1 \ \mu$ W. From  $C_g \leq 40 \ aF$  [4],  $g_m \gtrsim 15 \ \mu$ S and  $S_I/2e \leq 2 \ \mu$ A, we obtain  $\delta q_{rms} \leq 13 \ \mu e/\sqrt{\text{Hz}}$  for our double gate device which corresponds to an *rms* charge resolution of 0.4 electron in the 0.8 GHz bandwidth of our set-up. Within a factor five of the best resolution achieved in SETs [14], this smaller sensitivity of the present CNT-FETs, and more generally of nano-FETs, is balanced by a much larger bandwidth (0.8 GHz here against 0.08 GHz in [14]).

In conclusion, our comprehensive study of RF transport and shot noise in quasi-ballistic nanotube transistors has allowed to shed light on the hot electron regime in 1D transistors. In particular our data support to a generalized Johnson-Nyquist expression for thermal noise in 1D transistors. Finally we have benchmarked nanotube FETs against nanotube SETs as fast single electron detectors.

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FIG. 1: Double gate nanotube transistor with its measuring scheme (a) and its low frequency equivalent circuit (b). Nanotube diameter is about 2 nm. Transistors parameters are the channel resistance  $g_d^{-1}$ , the transconductance  $g_m$ , gate capacitance  $C_g$  and its geometrical and quantum contributions ( $C_{geo}$  and  $C_q$ ) and the noise current generator  $\delta i$ . In this lumped element description the channel potential,  $V_{ch} = V_g \times C_g/C_q$ , governs the barrier height  $\Phi = -e(V_{ch} + Const.)$  so that  $\beta = \partial \Phi/\partial V_g = C_g/C_q$ .



FIG. 2: Set of DC current (inset) and RF transconductance  $g_m^{RF}$  (main panel) of nanotube transistors as function of gate voltage.  $g_m^{RF}$  is deduced from transmission measurement in the 0-0.8 GHz bandwidth as explained in the text. Transconductance maximum reaches 30  $\mu$ S at  $V_g \simeq +0.5$  V. Low bias data ( $V_d = -(0.1, 0.2, 0.3)$  V) are fitted with Eq.(2) (solid lines) with a prefactor  $\simeq 0.6$  to account for non-ballistic transport. We obtain  $V_{Te} = k_B T_e/e\beta \simeq (0.12, 0.14, 0.17) \pm 0.01$  V which gives  $k_B T_e = (24, 26, 34)$  meV ( $\beta = 0.2$ ).



FIG. 3: Typical bias dependence of DC current and current noise of the nanotube transistor in the metallic state ( $V_g \leq 0$ ). Noise is obtained after substraction of a  $\propto 1/f^2$  Lorenzian tail in the measured noise spectrum (inset). It shows a poissonian behavior  $S_I/2e \simeq I_d$  for  $|V_d| < 0.4$  V and a saturation above.



FIG. 4: Bias dependence of DC current  $I_d$ , RF current noise  $S_I$  and RF transconductance  $g_m$  at the transconductance maximum ( $V_g \sim +0.5$  V).